

Silicon NPN Epitaxial

2SC4702

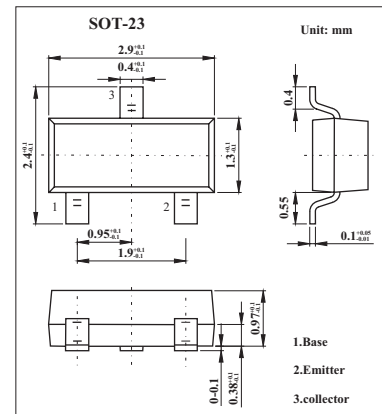
■ Features

- High breakdown voltage

$V_{CEO} = 300\text{ V}$

- Small Cob

$C_{ob} = 1.5\text{ pF Typ.}$

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	300	V
Collector-emitter voltage	V_{CEO}	300	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}$, $I_E = 0$	300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}$, $R_{BE} = \infty$	300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}$, $I_C = 0$	5			V
Collector cutoff current	I_{CBO}	$V_{CB} = 250\text{V}$, $I_E = 0$			0.1	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 30\text{mA}$, $I_B = 3\text{mA}$			0.5	V
DC current gain	h_{FE}	$V_{CE} = 6\text{V}$, $I_C = 2\text{mA}$	60		150	
Gain bandwidth product	f_T	$V_{CE} = 6\text{V}$, $I_C = 5\text{mA}$		80		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		1.5		pF

■ Marking

Marking	
	XV-